T-01-01
T-27-25

Switching/Amplifier Transistors

MOSFETs — N-Channel

PART NUMBER	PACKAGE	$V_{GS(TH)}$ V Min	$V_{GS(TH)}$ V Max	BV_{DSS} V Min	I_{DSS} pA Max	I_{GSS} pA Max	g_{fs} μmho Min	$r_{DS(ON)}$ Ω Max	$I_{D(ON)}$ mA Min	$I_{D(ON)}$ mA Max	COMMENTS
2N4351	TO-72	1.0	5.0	25	10nA	10	1000	300	3		High Input Z
3N170	TO-72	1.0	2.0	25	10nA	10	1000	200	10		High Input Z
3N171	TO-72	1.5	3.0	25	10nA	10	1000	200	10		High Input Z
IT1750	TO-72	0.5	3.0	25	10nA	10	3000	50	10		Low $r_{DS(ON)}$
M116	TO-72	1.0	5.0	30	10nA	100		100			Diode Protected
M117	TO-72	1.0	5.0	30	10nA	1		100			High Input Z

MOSFETs — P-Channel

Generally used where max. isolation between signal source and logic drive is required: switch "On" resistance varies with signal amplitude.

PART NUMBER	PACKAGE	$V_{GS(TH)}$ V Min	$V_{GS(TH)}$ V Max	BV_{DSS} V Min	I_{DSS} pA Max	I_{GSS} pA Max	g_{fs} μmho Min	$r_{DS(ON)}$ Ω Max	$I_{D(ON)}$ mA Min	$I_{D(ON)}$ mA Max	COMMENTS
2N4352	TO-72	−1.0	−5.0	−25	−10nA	10	1000	600	−3		High Input Z
3N163	TO-72	−2.0	−5.0	−40	−200	−10	2000	250	−5	−30	High Input Z
3N164	TO-72	−2.0	−5.0	−30	400	10	1000	300	−3	−30	High Input Z
3N172	TO-72	−2.0	−5.0	−40	−400	−200		250	−5	−30	Diode Protected
3N173	TO-72	−2.0	−5.0	−30	−10nA	−500		350	−5	−30	Diode Protected
IT1700	TO-72	−2.0	−5.0	−40	200		2000	400	−2		High Input Z
IT1701	TO-72	−2.0	−5.0	−40	200	100	2000	400	−2		Diode Protected

Diodes, Low Leakage Used to protect the inputs of MOSFETs such as 3N163, while maintaining input leakage < 0.1 pA.

PART NUMBER	PACKAGE	I_R@ 1V (pA) Typ	I_R@ 10 V, 125°C (nA) Max	BV_R@ 1μA (V) Min	V_F@ 10mA (V) Min	V_F@ 10mA (V) Max	COMMENTS
ID100	TO-78	0.1	10	30	0.8	1.1	(Note 1)
ID101	TO-71	0.1	10	30	0.8	1.1	(Note 1)

Note 1. Used to protect the inputs of MOSFETs such as 3N163, while maintaining input leakage < 0.1pA.